Mapping of Midgap States in Hydrogenated Amorphous Silicon from Photoluminescence Excitation Spectroscopy
We have determined:

• the 2-step excitation mode.
• the limiting transition $D^0/-$
• the excitation and radiative decay mode of the 0.8 eV PL
• the location and energy distribution of the $D^-$ states

We have provided strong evidence in favor of the Dangling Bond Model.